

ABSTRACT**Method for Fabricating a Semiconductor Substrate and Semiconductor Substrate**

The invention relates to a method for fabricating a semiconductor substrate comprising the steps of: providing a semiconductor on insulator type substrate, providing a diffusion barrier layer and providing a second semiconductor layer. By providing the diffusion barrier layer, it becomes possible to suppress diffusion from the highly doped first semiconductor layer into the second semiconductor layer. The invention also relates to a corresponding semiconductor substrate and opto-electronic devices comprising such a substrate.

- Figure 1 -